

TOSHIBA TRANSISTOR SILICON PNP EPITAXIAL TYPE (PCT PROCESS)

2SA1892

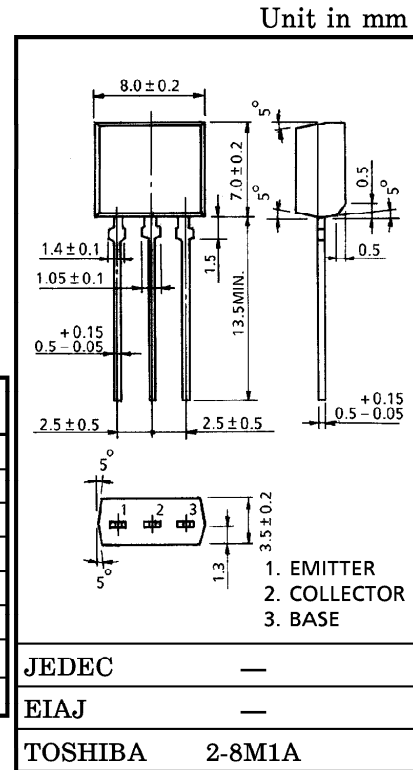
POWER AMPLIFIER APPLICATIONS

POWER SWITCHING APPLICATIONS

- Low Collector Saturation Voltage : $V_{CE(sat)} = -0.5V$ (Max.)
- High Power Dissipation : $P_C = 1.3W$
- High Speed Switching Time : $t_{stg} = 1.0\mu s$ (Typ.)
- Complementary to 2SC5029

MAXIMUM RATINGS ($T_a = 25^\circ C$)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	-50	V
Collector-Emitter Voltage	V_{CEO}	-50	V
Emitter-Base Voltage	V_{EBO}	-5	V
Collector Current	I_C	-3	A
Base Current	I_B	-0.2	A
Collector Power Dissipation	P_C	1.3	W
Junction Temperature	T_j	150	$^\circ C$
Storage Temperature Range	T_{stg}	-55~150	$^\circ C$



Weight : 0.55g (Typ.)

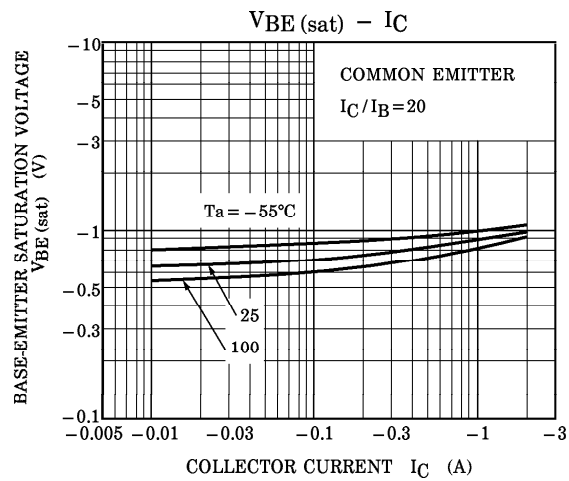
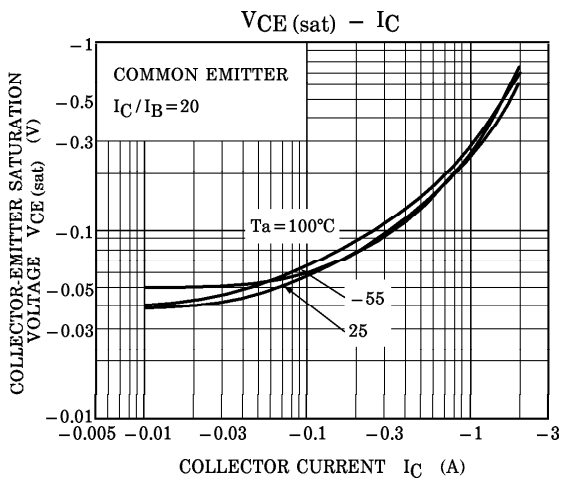
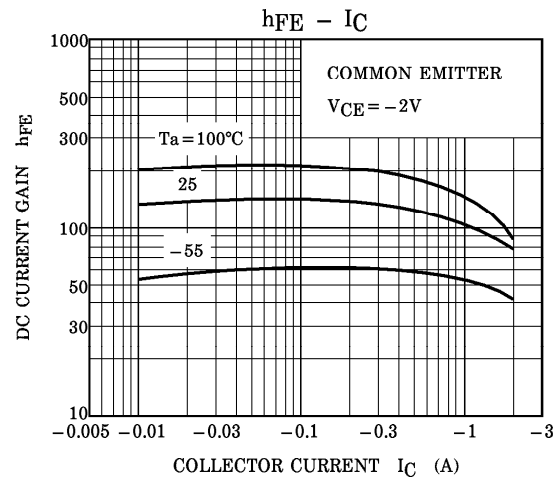
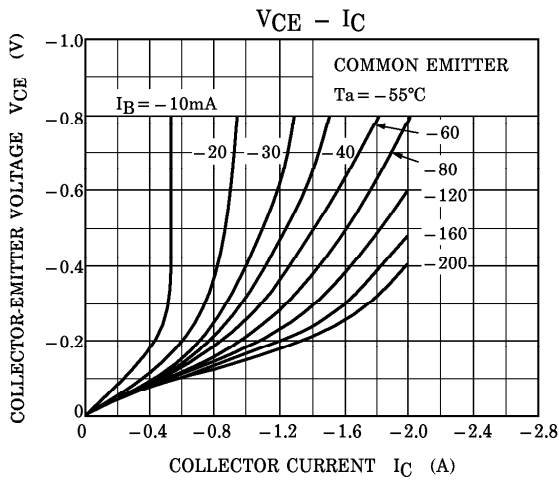
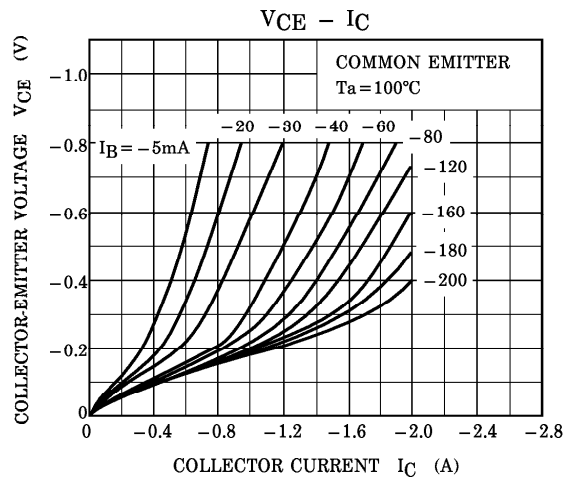
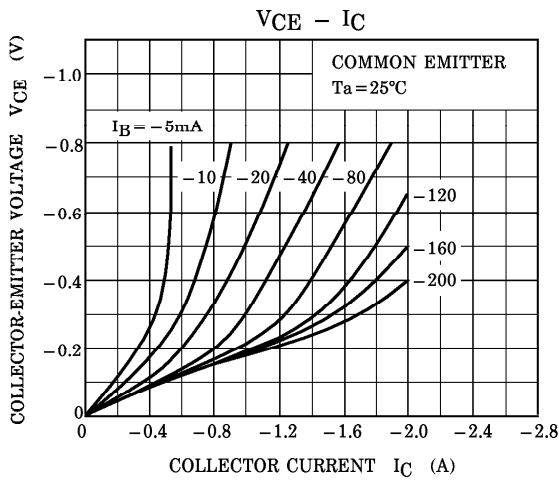
ELECTRICAL CHARACTERISTICS ($T_a = 25^\circ C$)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current		I_{CBO}	$V_{CB} = -50V, I_E = 0$	—	—	-1.0	μA
Emitter Cut-off Current		I_{EBO}	$V_{EB} = -5V, I_C = 0$	—	—	-1.0	μA
Collector-Emitter Breakdown Voltage		$V_{(BR)CEO}$	$I_C = -10mA, I_B = 0$	-50	—	—	V
DC Current Gain		$h_{FE(1)}$ (NOTE)	$V_{CE} = -2V, I_C = -0.5A$	70	—	240	
		$h_{FE(2)}$	$V_{CE} = -2V, I_C = -1.5A$	40	—	—	
Saturation Voltage	Collector-Emitter	$V_{CE(sat)}$	$I_C = -1A, I_B = -0.05A$	—	—	-0.5	V
	Base-Emitter	$V_{BE(sat)}$	$I_C = -1A, I_B = -0.05A$	—	—	-1.2	
Transition Frequency		f_T	$V_{CE} = -2V, I_C = -0.5A$	—	100	—	MHz
Collector Output Capacitance		C_{ob}	$V_{CB} = -10V, I_E = 0, f = 1MHz$	—	40	—	pF
Switching Time	Turn-on Time	t_{on}		—	0.1	—	μs
	Storage Time	t_{stg}		—	1.0	—	
	Fall Time	t_f		—	—	0.1	

Note : $h_{FE(1)}$ Classification O : 70~140, Y : 120~240

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